Vishay Siliconix

HALOGEN

FREE

6.5 m Ω , Bidirectional Switch in Compact WCSP

DESCRIPTION

The SiP32101, SiP32102, SiP32103, and SiP32104 are low resistance bidirectional load switches. They isolate A and B ports at off state. The parts have an ultra low 6.5 m Ω (typ. at 3.3 V) on-resistance and operate from a + 2.3 V to + 5.5 V input voltage range, making the devices ideal battery-disconnect switches for high capacity battery applications and multi-source power switches where bidirectional on/off control is required. The parts have identical A and B ports conducting current in both directions equally well.

The SiP32101, SiP32102, SiP32103, and SiP32104 have slew rate control minimizing switch on in-rush current in large load capacitor. These devices are also highly efficient, featuring low operating and shutdown currents.

The SiP32101, SiP32102, SiP32103, and SiP32104 can interface directly with a low voltage control signal. The SiP32101, SiP32103, and SiP32104 have an active low enable with different EN pull options. The SiP32102 has an active high enable. The series provides choices to minimize enable control circuit current depending on application requirement.

The SiP32101, SiP32102, SiP32103, and SiP32104 are available in an ultra compact 12-bump, 1.3 mm x 1.7 mm, 0.4 mm pitch WCSP package with top side lamination. The device operates over the temperature of -40 $^{\circ}$ C to +85 $^{\circ}$ C.

FEATURES

- · Bidirectional on and off
- 7 A continuous current capability
- Ultra low R_{on} , 6.5 m Ω (typ.) at 3.3 V
- Wide input voltage, 2.3 V to 5.5 V
- Slew rate controlled turn on
- Low guiescent current: 110 nA
- High / low EN, and integrated pull options
- Compact 12-bump, 1.3 mm x 1.7 mm x 0.55 mm WCSP package
- Material categorization: for definitions of compliance please see <u>www.vishav.com/doc?99912</u>

APPLICATIONS

- · Smartphones and tablets
- · Digital still / video cameras
- · Portable meters and test instruments
- · Communication devices with embedded batteries
- · Portable medical and healthcare systems
- · Data storage
- · Battery bank

TYPICAL APPLICATION CIRCUIT

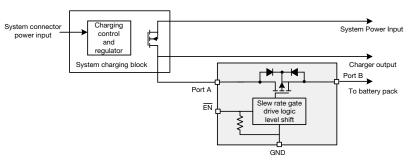


Fig. 1 - Typical Application Circuit

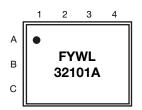
| ORDERING INFORMATION | | | | | | | |
|----------------------|---------|--------|----------------------|---------------------------------------|------------------|--|--|
| PART NUMBER | MARKING | ENABLE | ENABLE PULL RESISTOR | PACKAGE | TEMPERATURE | | |
| SiP32101DB-T1-GE1 | 32101A | Low | Enable pull low | | | | |
| SiP32102DB-T1-GE1 | 32102A | High | Enable pull low | 12-bump, 1.3 mm x 1.7 mm, | -40 °C to +85 °C | | |
| SiP32103DB-T1-GE1 | 32103A | Low | Enable pull high | 0.4 mm pitch WCSP package | | | |
| SiP32104DB-T1-GE1 | 32104A | Low | No pull | , , , , , , , , , , , , , , , , , , , | | | |
| SiP32101EVB | - | - | - | | - | | |
| SiP32102EVB | - | - | - | Evaluation board | = | | |
| SiP32103EVB | - | - | = | Evaluation board | - | | |
| SiP32104EVB | - | - | = | | = | | |

Note

GE1 denotes halogen-free and RoHS-compliant

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MARKING FORMAT



| ABSOLUTE MAXIMUM RATINGS | | | | | | |
|------------------------------------------|----------------------------------|-------------|------|--|--|--|
| PARAMETER | CONDITIONS | LIMIT | UNIT | | | |
| W. W. | Reference to GND | -0.3 to +6 | | | | |
| V _{PA} , V _{PB} | Pulse at 1 ms reference to GND a | -1.6 | V | | | |
| V _{EN} | Reference to GND | -0.3 to +6 | | | | |
| Maximum continuous switch current 7 | | | | | | |
| Maximum pulse current | 100 μs pulse | 15 | A | | | |
| ESD (HBM) | | 8000 | V | | | |
| Operating temperature | | -40 to +85 | | | | |
| Operating junction temperature | | 125 | °C | | | |
| Storage temperature | | -65 to +150 | | | | |
| Thermal resistance (θ _{JA}) b | | 73 | °C/W | | | |
| Power dissipation (P _D) b, c | T _A = 70 °C | 1096 | mW | | | |

Notes

- a. Negative current injection up to 300 mA
- b. All bumps soldered to 1" x 1", 2 oz. copper, 4 layers PC board
- c. Derate 13.7 mW/ $^{\circ}$ C above T_A = 70 $^{\circ}$ C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating/conditions for extended periods may affect device reliability.

| SPECIFICATIONS | | | | | | | |
|-----------------------------------------|---------------------|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|----------|--------|--------|------|--|
| | | TEST CONDITIONS UNLESS SPECIFIED | LIMITS | | | | |
| PARAMETER | SYMBOL | $ \begin{array}{c} V_{IN} = V_{PA}/V_{PB} = 2.3 \text{ V to } 5.5 \text{ V, } T_A = -40 \text{ °C to } 85 \text{ °C} \\ (\text{Typical values are at } V_{PA}, V_{PB} = 4.2 \text{ V,} \\ C_{PA}, C_{PB} = 0.1 \mu\text{F, } T_A = 25 \text{ °C)} \end{array} $ | | TYP. b | MAX. a | UNIT | |
| Power Supply | | | | | | | |
| Operating voltage ^c | $V_{PA/PB}$ | | 2.3 | - | 5.5 | V | |
| Quiescent current | IQ | $V_{\overline{EN}}$ = 0 V (for SiP32101 and SiP32104), V_{EN} = V _{IN} (for SiP32102), no load | | 110 | 140 | nA | |
| | | $V_{\overline{EN}} = 0 \text{ V (for SiP32103)},$ no load | | 8.2 | 15 | μΑ | |
| Shutdown current | I _{SHDN} | $V_{\overline{EN}} = V_{IN}$ (for SiP32101, SiP32103, and SiP32104), $V_{EN} = 0$ V (for SiP32102), no load | | 110 | 140 | nA | |
| Internal FET | | | | | | | |
| On-resistance | B | $V_{PA}/V_{PB} = 2.3 \text{ V}, I_L = 500 \text{ mA}, T_A = 25 \text{ °C}$ | - | 8 | 13 | mΩ | |
| On-resistance | R _{DS(on)} | $V_{PA}/V_{PB} = 3.3 \text{ V}, I_L = 500 \text{ mA}, T_A = 25 \text{ °C}$ | - 6.5 10 | | 11122 | | |
| Control | | | | | | | |
| EN input logic-low voltage ^c | V_{IL} | | - | - | 0.4 | V | |
| EN input logic-high voltage c | V_{IH} | | 1.4 | - | - | V | |
| EN input logic hysteresis | V _{I(HYS)} | | - | > 200 | - | mV | |
| EN pull resistor | $R_{\overline{EN}}$ | $V_{PA}/V_{PB} = 5.5 \text{ V}, V_{\overline{EN}} \text{ (or } V_{EN}) = 2.3 \text{ V}$ | 350 | 500 | 700 | kΩ | |



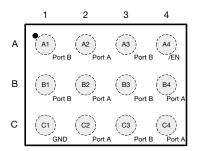
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| SPECIFICATIONS | | | | | | | |
|----------------------------|---------------------|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|--------|--------|--------|------|--|
| | | TEST CONDITIONS UNLESS SPECIFIED | | LIMITS | | | |
| PARAMETER | SYMBOL | $\begin{split} V_{IN} &= V_{PA}/V_{PB} = 2.3 \text{ V to } 5.5 \text{ V, } T_A = -40 \text{ °C to } 85 \text{ °C} \\ &(\text{Typical values are at } V_{PA}, V_{PB} = 4.2 \text{ V,} \\ &C_{PA}, C_{PB} = 0.1 \mu\text{F, } T_A = 25 \text{ °C)} \end{split}$ | MIN. a | TYP. b | MAX. a | UNIT | |
| Timing | | | | | | | |
| Output turn-on delay time | t _{d(on)} | | - | 0.8 | - | | |
| Output turn-on rise time | t _r | $V_{IN} = 4.2 \text{ V}, R_{I} = 100 \Omega, C_{I} = 0.1 \mu\text{F}, T_{\Delta} = 25 \text{ °C}$ | - | 1 | - | ms | |
| Output turn-off delay time | t _{d(off)} | $v_{IN} = 4.2 v, \ n_L = 100 22, \ O_L = 0.1 \ \mu\text{F}, \ I_A = 25 C$ | - | 0.12 | - | 1115 | |
| Output turn-off fall time | t _f | | ı | 0.1 | - | | |

Notes

- a. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum
- b. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing
- c. For V_{IN} outside this range consult typical \overline{EN} , EN threshold curve

BUMP CONFIGURATION



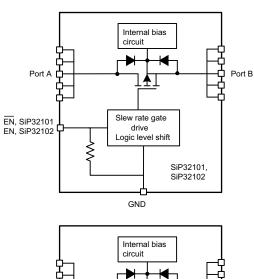
Top view (solder bumps on bottom)

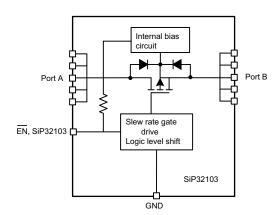
Fig. 2 - WCSP12, 1.3 mm x 1.7 mm

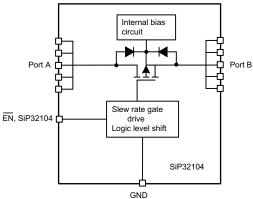
| BUMP DESCRIPTION | | | | | |
|--------------------|------|---------------------------------|--|--|--|
| BUMP NUMBER | NAME | FUNCTION | | | |
| A1, B1, A3, B3, C3 | PB | Power port B | | | |
| C1 | GND | Ground | | | |
| A2, B2, C2, B4, C4 | PA | Power port A | | | |
| A4 | ĒN | Switch enable input, active low | | | |

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FUNCTIONAL BLOCK DIAGRAM







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TYPICAL CHARACTERISTICS (internally regulated 25 °C, unless otherwise noted)

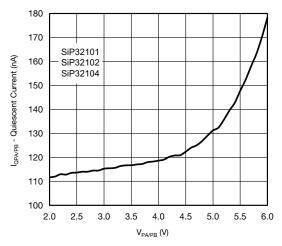


Fig. 3 - Quiescent vs. Input Voltage

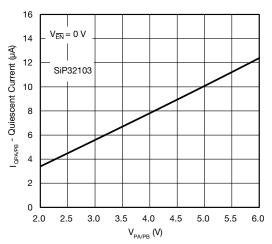


Fig. 4 - Quiescent vs. Input Voltage

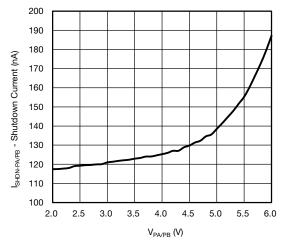


Fig. 5 - Shutdown Current vs. Input Voltage

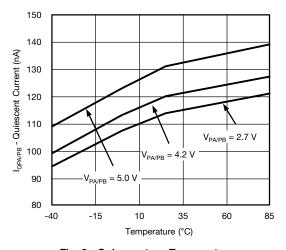


Fig. 6 - Quiescent vs. Temperature

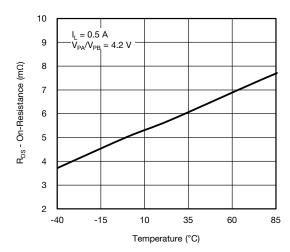


Fig. 7 - On Resistance vs. Temperature

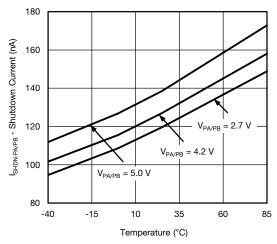


Fig. 8 - Shutdown Current vs.Temperature

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TYPICAL CHARACTERISTICS (internally regulated 25 °C, unless otherwise noted)

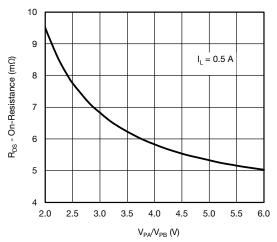


Fig. 9 - On Resistance vs. Input Voltage

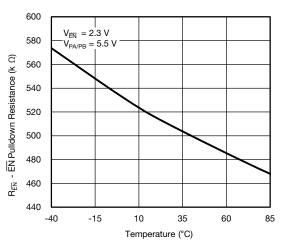


Fig. 10 - EN Pull Down Resistance vs. Temperature

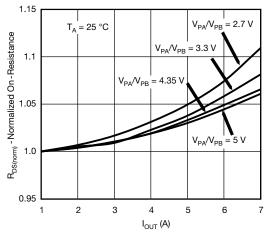


Fig. 11 - Normalized On Resistance vs. Load Current

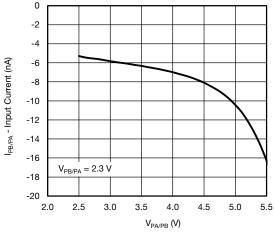


Fig. 12 - Reverse Blocking Current (I_{RB}) vs. Output Voltage

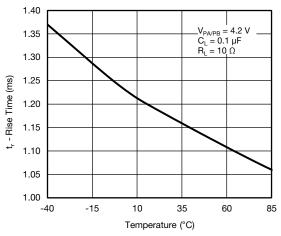


Fig. 13 - Rise Time vs. Temperature

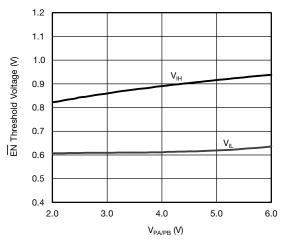


Fig. 14 - EN Threshold Voltage vs. Input Voltage

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TYPICAL CHARACTERISTICS (internally regulated 25 °C, unless otherwise noted)

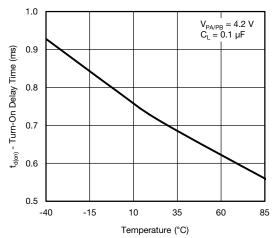


Fig. 15 - Turn-on Delay Time vs. Temperature

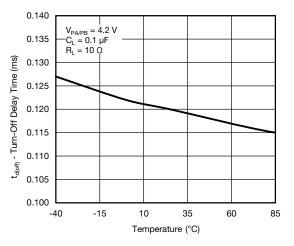


Fig. 16 - Turn-off Delay Time vs. Temperature

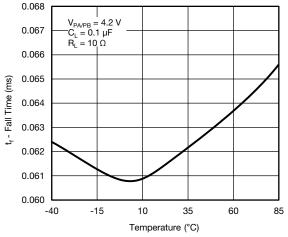


Fig. 17 - Fall Time vs. Temperature

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DETAILED DESCRIPTION

The SiP32101 bidirectional switch features reverse blocking capability to isolate the battery from the system. The internal switch has an ultra low 6.5 m Ω (typ. at 3.3 V) on-resistance and operates from a +2.3 V to +5.5 V input voltage range, making the device ideal battery disconnect-switch for high capacity battery applications. The parts can handle 7 A continuous current at both directions.

The SiP32101 has slew rate control, making it ideal in large load capacitor as well as high current load switching applications.

The SiP32101 is available in an ultra compact 12-bump, 1.3 mm x 1.7 mm, 0.4 mm pitch WCSP package with top side lamination. The device operates over the temperature of -40 °C to +85 °C.

REVERSE CURRENT BLOCKING

The SiP32101 is a bidirectional switch that prevent current flowing from either port to the other when the device is disabled.

EN INPUT

SiP32101 has an active-low enable pin which can interface with low voltage GPIO directly. The switch is on when EN is low and off when EN is high. The SiP32101 has an integrated pull down resistor at $\overline{\text{EN}}$ pin.

SWITCH ON AND OFF PERFORMANCE

The SiP32101 has a slew rate control. This minimizes the inrush current and provides a soft turn on.

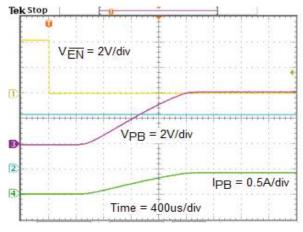


Fig. 18 - Port B Turn-On Time (V_{PA} = 4.2 V, R_L = 10 Ω , C_L = 0.1 μ F)

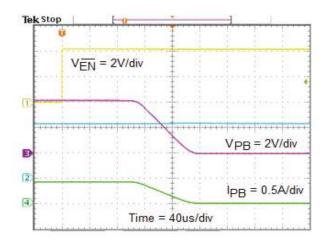


Fig. 19 - Port B Turn-Off Time (V_{PA} = 4.2 V, R_L = 10 Ω , C_L = 0.1 μ F)

DEVICE PIN OUT

Device pin out is designed for ease of layout.

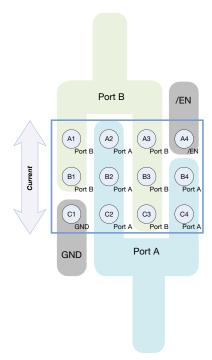


Fig. 20 - Proposed Layout





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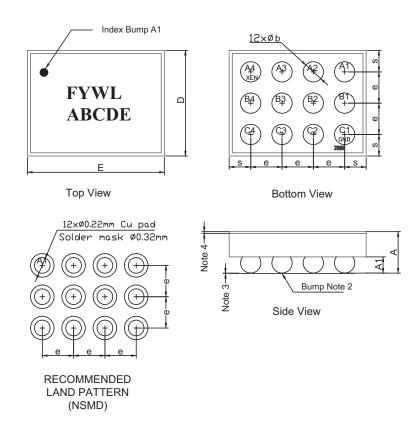
| PRODUCT SUMMARY | | | | | | |
|---------------------------------------------------|---------------------------------------------------------------------------------------------------------------|----------------------------------------------------------------------------------------------------------------|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------------------------------------------------------------------------|--|--|
| Part number | SiP32101 | SiP32102 | SiP32103 | SiP32104 | | |
| Description | 2.3 V to 5.5 V, 6.5 mΩ, 7 A, bidirectional switch, EN active low with internal pull-down resistor | 2.3 V to 5.5 V, 6.5 mΩ, 7 A, bidirectional switch, EN active high with internal pull-down resistor | $\begin{array}{c} 2.3\text{V to}5.5\text{V},6.5\text{m}\Omega,\\ 7\text{A, bidirectional}\\ \text{switch, EN active low}\\ \text{with internal pull-up}\\ \text{resistor} \end{array}$ | 2.3 V to 5.5 V, 6.5 mΩ, 7 A, bidirectional switch, EN active low | | |
| Configuration | Single | Single Single Singl | | Single | | |
| Slew rate time (µs) | 1 000 | 1 000 | 1 000 | 1 000 | | |
| On delay time (µs) | 500 | 500 | 800 | 800 | | |
| Input voltage min. (V) | 2.3 | 2.3 | 2.3 | 2.3 | | |
| Input voltage max. (V) | 5.5 | 5.5 | 5.5 | 5.5 | | |
| On-resistance at input voltage min. (m Ω) | 8 | 8 | 8 | 8 | | |
| On-resistance at input voltage max. (m Ω) | 5.1 | 5.1 | 5.1 | 5.1 | | |
| Quiescent current at input voltage min. (µA) | 0.11 | 0.11 | 4 | 0.11 | | |
| Quiescent current at input voltage max. (µA) | 0.14 | 0.14 | 8.2 | 0.14 | | |
| Output discharge (yes / no) | No | No | No | No | | |
| Reverse blocking (yes / no) | Yes | Yes | Yes | Yes | | |
| Continuous current (A) | 7 | 7 | 7 | 7 | | |
| Package type | WCSP12 | WCSP12 | WCSP12 | WCSP12 | | |
| Package size (W, L, H) (mm) | 1.3 x 1.7 x 0.5 | 1.3 x 1.7 x 0.5 | 1.3 x 1.7 x 0.5 | 1.3 x 1.7 x 0.5 | | |
| Status code | 2 | 2 | 2 | 2 | | |
| Product type | Slew rate, true bidirectional | Slew rate, true bidirectional | Slew rate, true bidirectional | Slew rate, true bidirectional | | |
| Applications | Computers, consumer, industrial, healthcare, portable | Computers, consumer, industrial, healthcare, portable | Computers, consumer, industrial, healthcare, portable | Computers, consumer, industrial, healthcare, portable | | |

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg278628.

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WCSP12: 12 Bumps

(3 x 4, 0.4 mm pitch, 208 µm bump height, 1.71 mm x 1.31 mm die size)



| | MILLIMETERS (5) | | | INCHES | | | |
|-----------|-----------------|-------|-------|--------|--------|--------|--|
| DIMENSION | MIN. | NOM. | MAX. | MIN. | NOM. | MAX. | |
| А | 0.515 | 0.530 | 0.545 | 0.0203 | 0.0209 | 0.0215 | |
| A1 | 0.183 | 0.208 | 0.233 | 0.0072 | 0.0082 | 0.0092 | |
| b | 0.234 | 0.260 | 0.312 | 0.0092 | 0.0102 | 0.0123 | |
| е | | 0.400 | | | 0.0157 | | |
| S | 0.235 | 0.255 | 0.275 | 0.0093 | 0.0100 | 0.0108 | |
| D | 1.270 | 1.310 | 1.350 | 0.0500 | 0.0516 | 0.0531 | |
| E | 1.670 | 1.710 | 1.750 | 0.0657 | 0.0673 | 0.0689 | |

Notes (unless otherwise specified)

- (1) Laser mark on the silicon die back coated with an epoxy film.
- (2) Bumps are SAC396.
- (3) 0.050 max. co-planarity.
- (4) Laminate tape thickness is 0.022 mm.
- (5) Use millimeters as the primary measurement.

ECN: S13-2510-Rev. B, 16-Dec-13

DWG: 6017



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